December 1994

# 54F/74F32 Quad 2-Input OR Gate

### **General Description**

### **Features**

This device contains four independent gates, each of which performs the logic OR function.

■ Guaranteed 4000V minimum ESD protection

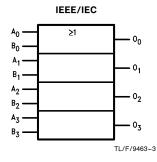
Commercial	Military	Package Number	Package Description
74F32PC		N14A	14-Lead (0.300" Wide) Molded Dual-In-Line
	54F32DM (Note 2)	J14A	14-Lead Ceramic Dual-In-Line
74F32SC (Note 1)		M14A	14-Lead (0.150" Wide) Molded Small Outline, JEDEC
74F32SJ (Note 1)		M14D	14-Lead (0.300" Wide) Molded Small Outline, EIAJ
	54F32FM (Note 2)	W14B	14-Lead Cerpack
	54F32LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

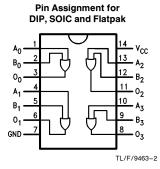
Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

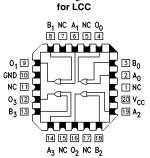
Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

### **Logic Symbol**

### **Connection Diagrams**







Pin Assignment

TI /F/9463-1

### **Unit Loading/Fan Out**

		54F/74F				
Pin Names	Description	U.L. HIGH/LOW	Input I <sub>IH</sub> /I <sub>IL</sub> Output I <sub>OH</sub> /I <sub>OL</sub>			
A <sub>n</sub> , B <sub>n</sub> O <sub>n</sub>	Inputs Outputs	1.0/1.0 50/33.3	20 μA/ – 0.6 mA – 1 mA/20 mA			

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### **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Storage Temperature} & -65^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to} + 125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to} + 175^{\circ}\mbox{C} \\ \mbox{Plastic} & -55^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \end{array}$ 

 $V_{CC}$  Pin Potential to

 Ground Pin
 −0.5V to +7.0V

 Input Voltage (Note 2)
 −0.5V to +7.0V

 Input Current (Note 2)
 −30 mA to +5.0 mA

Voltage Applied to Output

in HIGH State (with  $V_{CC} = 0V$ )

 $\begin{array}{ll} \mbox{Standard Output} & -0.5\mbox{V to V}_{CC} \\ \mbox{TRI-STATE} \mbox{$^{\circ}$ Output} & -0.5\mbox{V to } +5.5\mbox{V} \end{array}$ 

Current Applied to Output in LOW State (Max) twice the rated I<sub>OL</sub> (mA) ESD Last Passing Voltage (Min) 4000V

**Note 1:** Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

# Recommended Operating Conditions

Free Air Ambient Temperature

Supply Voltage

Military +4.5V to +5.5V Commercial +4.5V to +5.5V

### **DC Electrical Characteristics**

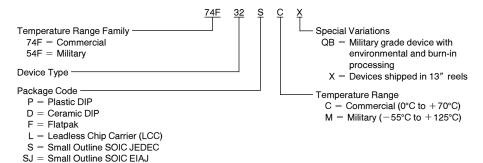
Symbol	Parameter		54F/74F			Units	V <sub>CC</sub>	Conditions	
Symbol			Min	Тур	Max	Onits	VCC	Conditions	
$V_{IH}$	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
$V_{IL}$	Input LOW Voltage				0.8	V		Recognized as a LOW Signal	
$V_{CD}$	Input Clamp Diode Voltage				-1.2	V	Min	$I_{IN} = -18 \text{ mA}$	
V <sub>OH</sub>	Output HIGH Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub> 74F 5% V <sub>CC</sub>	2.5 2.5 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub>			0.5 0.5	٧	Min	$I_{OL} = 20 \text{ mA}$ $I_{OL} = 20 \text{ mA}$	
I <sub>IH</sub>	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	V <sub>IN</sub> = 2.7V	
I <sub>BVI</sub>	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V <sub>IN</sub> = 7.0V	
I <sub>CEX</sub>	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
V <sub>ID</sub>	Input Leakage Test	74F	4.75			٧	0.0	$I_{\text{ID}} = 1.9  \mu\text{A}$ All Other Pins Grounded	
I <sub>OD</sub>	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV All Other Pins Grounded	
I <sub>IL</sub>	Input LOW Current				-0.6	mA	Max	V <sub>IN</sub> = 0.5V	
los	Output Short-Circuit Current		-60		<b>-150</b>	mA	Max	V <sub>OUT</sub> = 0V	
I <sub>CCH</sub>	Power Supply Current			6.1	9.2	mA	Max	V <sub>O</sub> = HIGH	
I <sub>CCL</sub>	Power Supply Curren		10.3	15.5	mA	Max	V <sub>O</sub> = LOW		

### **AC Electrical Characteristics**

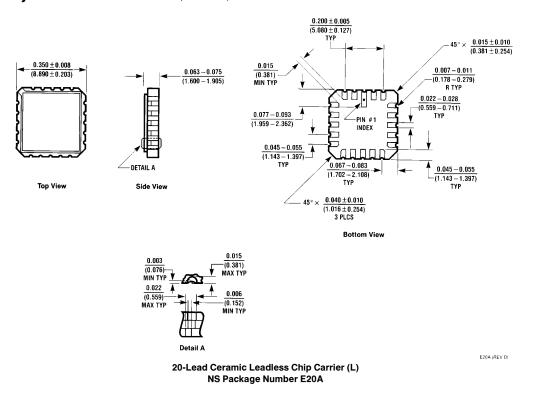
Symbol	Parameter	74F			54F		74F		Units
		$\begin{aligned} \textbf{T}_{\textbf{A}} &=  +25^{\circ}\textbf{C} \\ \textbf{V}_{\textbf{CC}} &=  +5.0\textbf{V} \\ \textbf{C}_{\textbf{L}} &=  50\textbf{pF} \end{aligned}$			$ extsf{T}_{ extsf{A}},  extsf{V}_{ extsf{CC}} =  extsf{Mil} \  extsf{C}_{ extsf{L}} =  extsf{50 pF}$		extstyle  ext		
		Min	Тур	Max	Min	Max	Min	Max	
t <sub>PLH</sub>	Propagation Delay	3.0	4.2	5.6	3.0	7.5	3.0	6.6	ne
$t_{PHL}$	$A_n$ , $B_n$ to $O_n$	3.0	4.0	5.3	2.5	7.5	3.0	6.3	ns

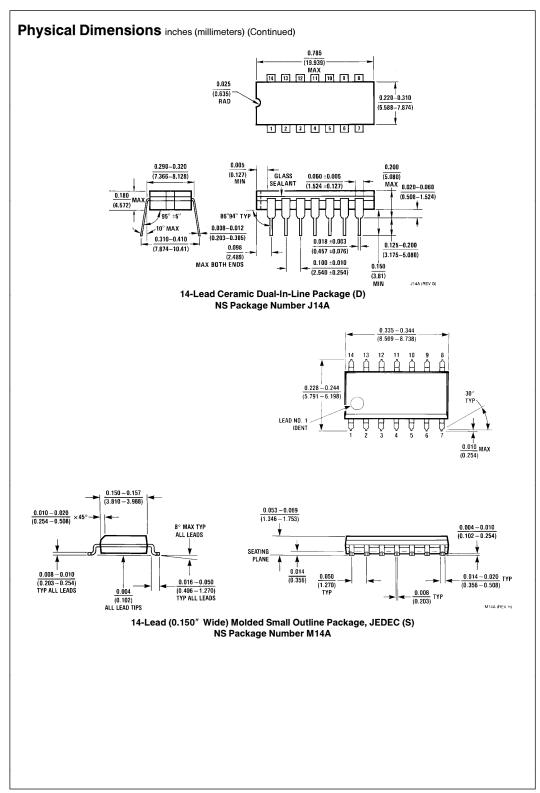
## **Ordering Information**

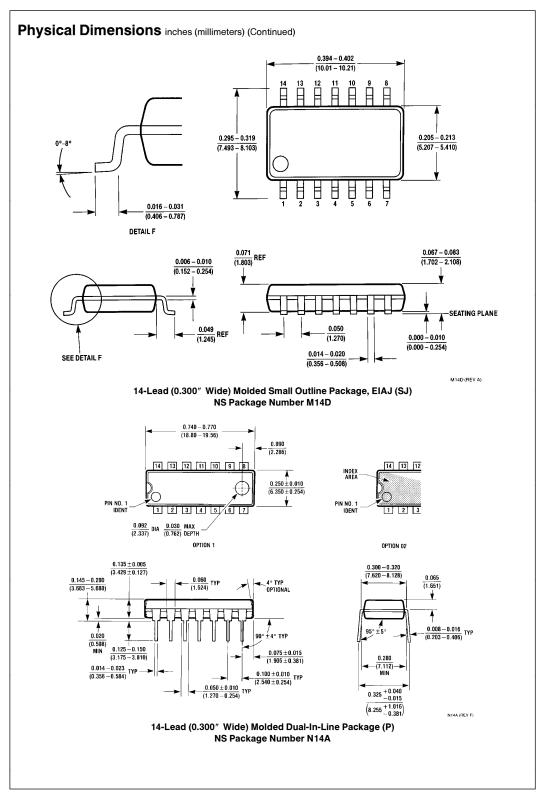
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:



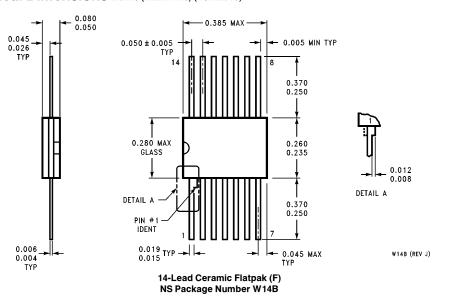
### Physical Dimensions inches (millimeters)







### Physical Dimensions inches (millimeters) (Continued)



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